

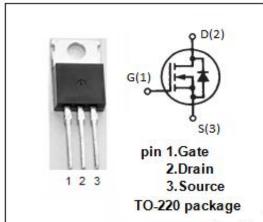
# isc N-Channel MOSFET Transistor

## FDP075N15A

#### **FEATURES**

- Drain Current : I<sub>D</sub> =130A@ T<sub>C</sub>=25 °C
- · Drain Source Voltage
  - : V<sub>DSS</sub>= 150V(Min)
- · Static Drain-Source On-Resistance
  - :  $R_{DS(on)} = 7.5 \text{ m} \Omega \text{ (Max)} @V_{GS} = 10V$
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation





### **DESCRIPTION**

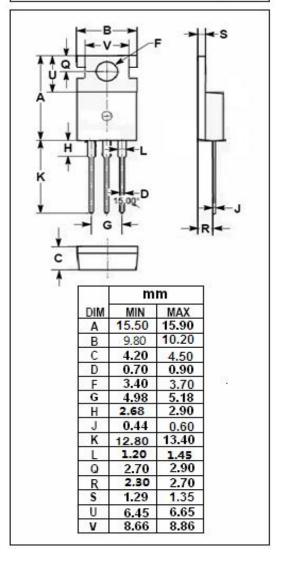
• motor drive, DC-DC converter, power switch and solenoid drive.

### ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

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PARAMETER	VALUE	UNIT					
Drain-Source Voltage	150	V					
Gate-Source Voltage-Continuous	±20	V					
Drain Current-Continuous	130	А					
Drain Current-Single Pluse	522	А					
Total Dissipation @T <sub>C</sub> =25℃	333	W					
Max. Operating Junction Temperature	-55~175	$^{\circ}$					
Storage Temperature	-55~175	$^{\circ}$					
	Drain-Source Voltage  Gate-Source Voltage-Continuous  Drain Current-Continuous  Drain Current-Single Pluse  Total Dissipation @T <sub>C</sub> =25°C  Max. Operating Junction Temperature	Drain-Source Voltage150Gate-Source Voltage-Continuous $\pm 20$ Drain Current-Continuous130Drain Current-Single Pluse $522$ Total Dissipation @ $T_C$ =25°C333Max. Operating Junction Temperature $-55\sim175$					

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	0.45	°C/W





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#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0; I <sub>D</sub> = 0.25mA	150	-	V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> ; I <sub>D</sub> = 0.25mA	2.0	4.0	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> =10V; I <sub>D</sub> =100A	-	7.5	m Ω
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> = ±20V;V <sub>DS</sub> = 0	-	±100	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =120V; V <sub>GS</sub> = 0	-	1.0	uA
V <sub>SD</sub>	Forward On-Voltage	I <sub>S</sub> =100A; V <sub>GS</sub> = 0	-	1.25	V

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